

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, *et al.* Docket No.: TSM03-0660
Serial No.: 10/699,574 Art Unit: TBD
Filed: October 31, 2003 Examiner: TBD
For: Strained Silicon Structure

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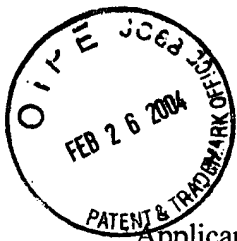
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PTO/SB/08A with 76 References Cited (5 pages)
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Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, *et al.* Attorney Docket: TSM03-0660
Filed: October 31, 2003 Examiner: TBD
Serial No.: 10/699,574 Art Unit: 2811
For: STRAINED SILICON STRUCTURE

Commissioner for Patents
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INFORMATION DISCLOSURE STATEMENT

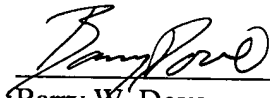
The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

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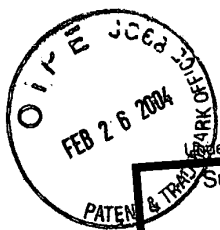
Cite numbers 1-45 are newly cited prior art being filed under the waived requirement of 37 CFR 1.98 (a)(2)(i) dated July 11, 2003, therefore, copies of these U.S. patents are not included.

Respectfully submitted,

2/23/2004
Date


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PTO/SB/08A (05-03)

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/699,574
Filing Date	October 31, 2003
First Named Inventor	Ge, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM03-0660

Sheet 1 of 5

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	1	US-4,072,974	02-07-1978	Ipri	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-5,013,681	05-07-1991	Godbey, et al.	
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				Application Number	10/699,574
				Filing Date	October 31, 2003
				First Named Inventor	Ge, <i>et al.</i>
				Art Unit	2811
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0660
Sheet	2	of	5		

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FOREIGN PATENT DOCUMENTS					
Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
	Country Code ³ - Number ⁴ - Kind Code ⁵ (<i>if known</i>)				
46	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

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Sheet	3	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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				Art Unit	2811
				Examiner Name	TBD
Sheet	4	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	²
	60	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
	61	SCHÜPPEN, A., <i>et al.</i> , "Mesa and Planar SiGe-HBTs on MBE-Wafers," Journal of Materials Science: Materials in Electronics, Vol. 6, (1995), pp. 298-305.	
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	63	CURRENT, M.I., <i>et al.</i> , "Atomic-Layer Cleaving and Non-Contact Thinning and Thickening for Fabrication of Laminated Electronic and Photonic Materials," 2001 Materials Research Society Spring Meeting (April 16-20, 2001).	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached.

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MAITI, C.K. & ARMSTRONG, G.A. (2001) *Applications of Silicon-Germanium Heterostructure Devices*. Philadelphia, PA: Institute of Physics Publishing.

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